

Lab-test measurements at CERN

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3D/FBK sensors meeting
16.7.2010

Systematic Lab-test measurements

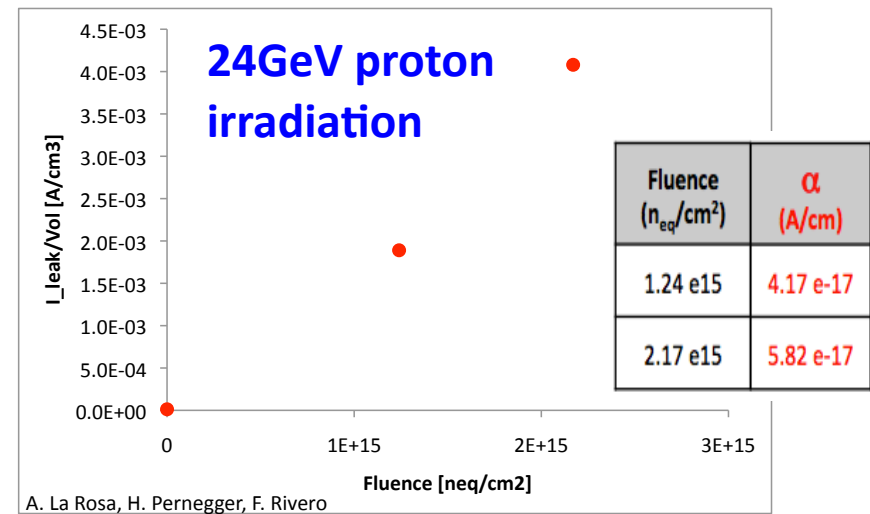
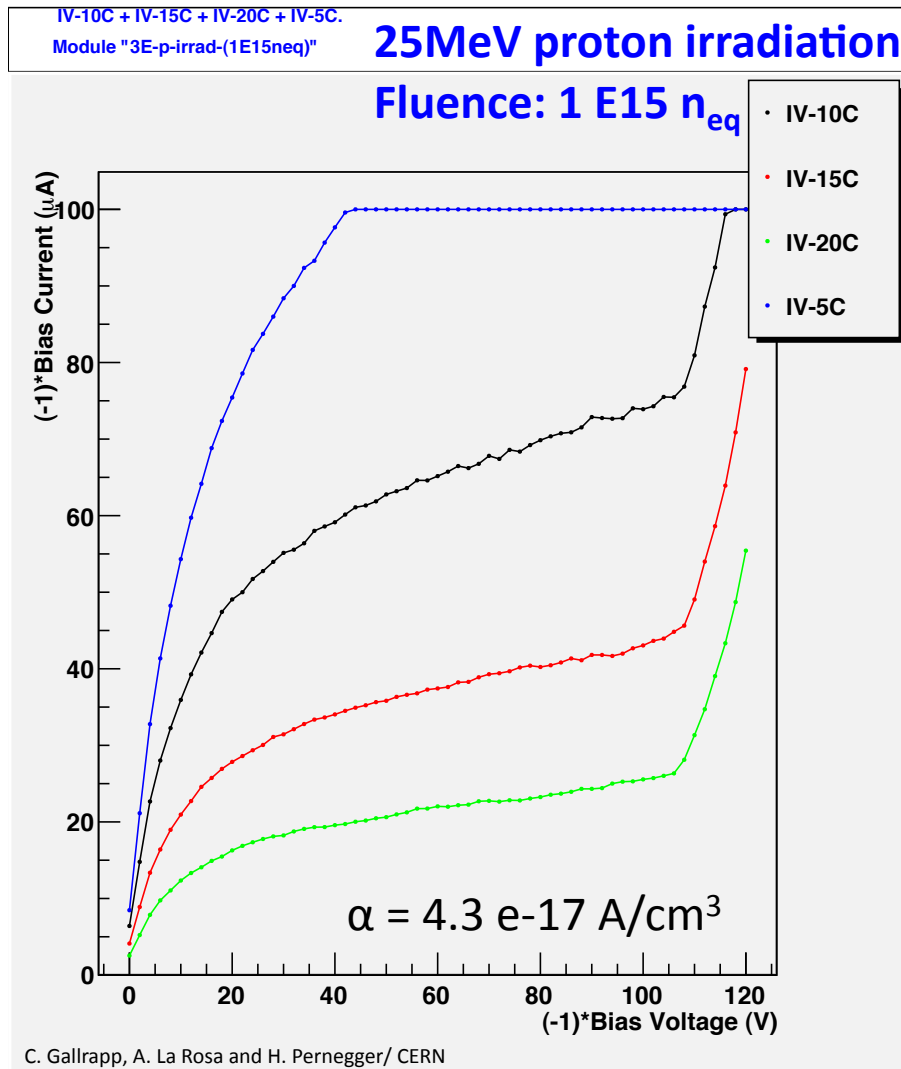
<https://twiki.cern.ch/twiki/bin/view/Main/CernAtlasPixelSensorsRD>

Same measurements with Planar (n-in-n and n-in-p), 3D-Si and Diamond (pCVD and scCVD):

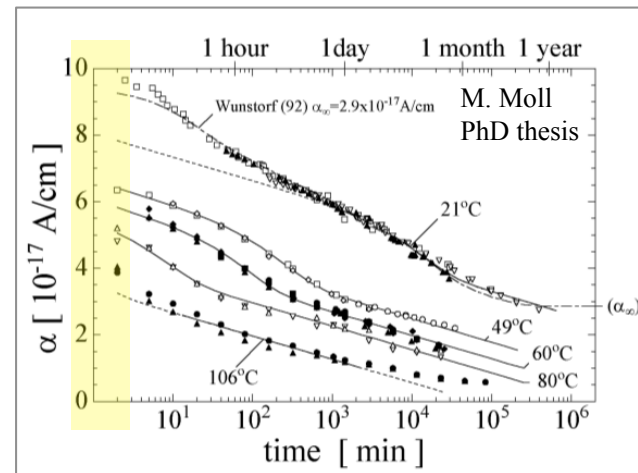
- **IV scan:** to measure the leakage current and to check for sensor damage and/or HV shorts.
 - Scan performed at different temperatures for irradiated devices
 - $I_{\text{leak}}/V_{\text{ol}}$ vs fluence estimation
 - Estimation of damage rate α
- **Monleak scan:** to measure of each pixel leakage current to look for excess due to localized earlier sensor breakdown
- **Minimal operational threshold:** to study the influence of the sensor capacitance on the minimal threshold.
- **Threshold and noise scan** (e.g.: with 60 ToT at 20ke and $T_h=3.2\text{ke}$)
- **Noise vs bias voltages**
 - at different temperatures for irradiated devices
- **Noise occupancy studies**
- **Crosstalk scan**
- **Gamma source test (Am241 and Cd109) self triggered** at different bias voltage
 - at different temperatures for irradiated devices
- **Beta source test (Sr90) external triggered** at different bias voltage
 - charge collection and charge sharing studies at different bias voltages
 - at different temperatures for irradiated devices

Leakage current studies

- 3D/FBK 3E-type

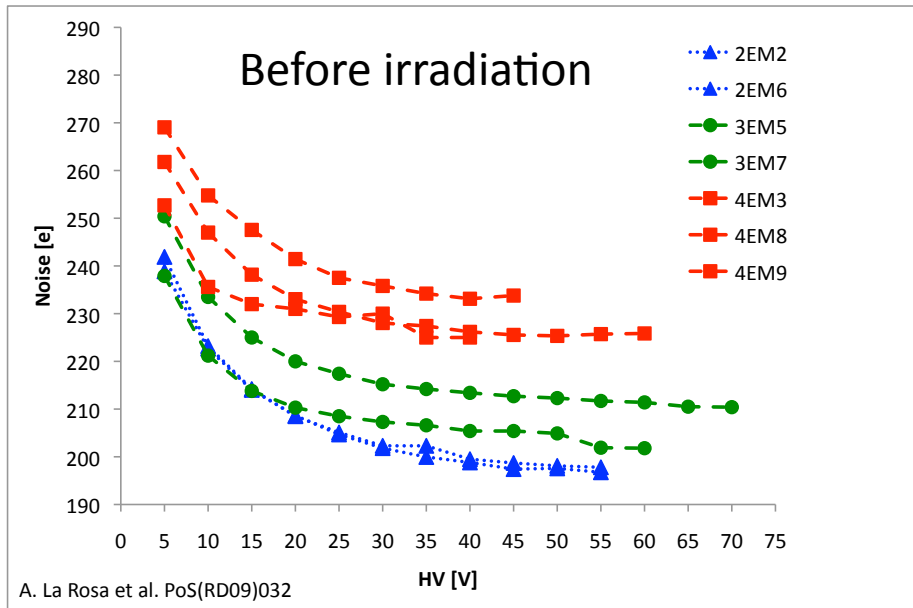


$$\frac{I_{Vol}}{Vol} = \frac{I_{Vol, \phi=0}}{Vol} + \alpha \phi$$



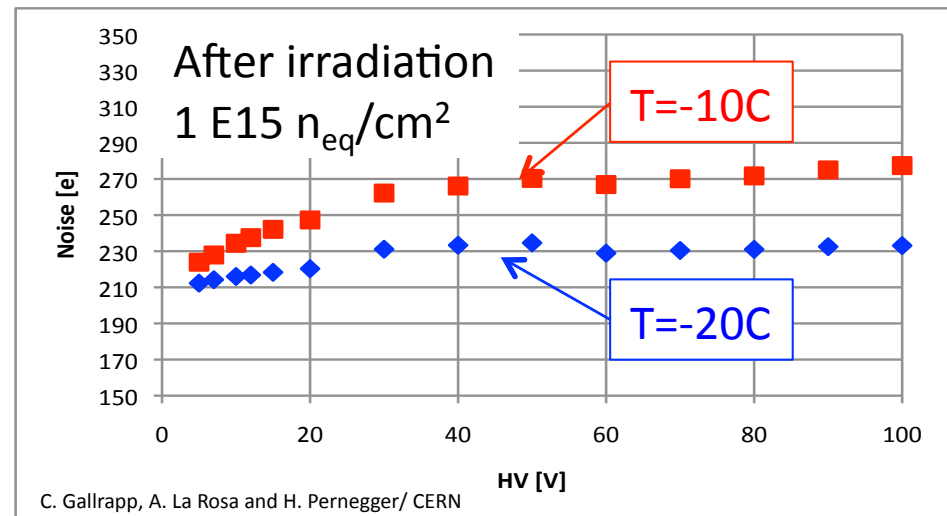
Threshold and noise measurements

- 3D/FBK sensors
- FE tuned with 60 ToT at 20ke and Th=3.2ke



	Threshold [e]	Noise [e]	T [C]
Before irradiation	3292 ± 57	214 ± 8	+ 22
After irradiation	3152 ± 145	231 ± 14	- 20

C_low and C_high measured after irradiation

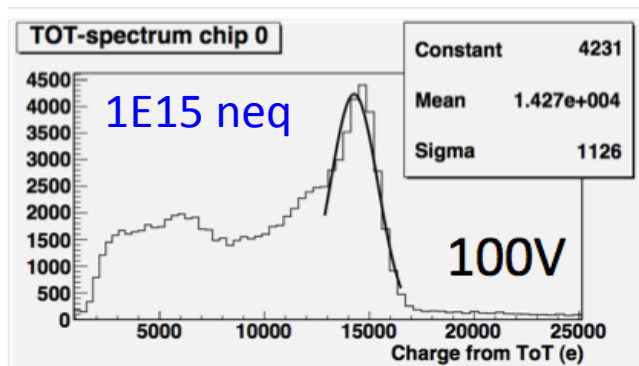
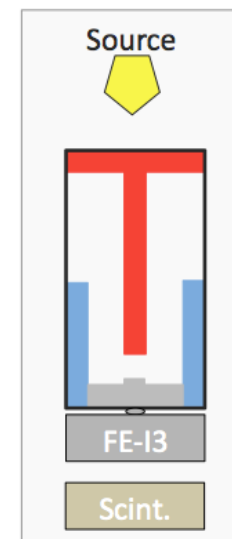


Source-test measurements

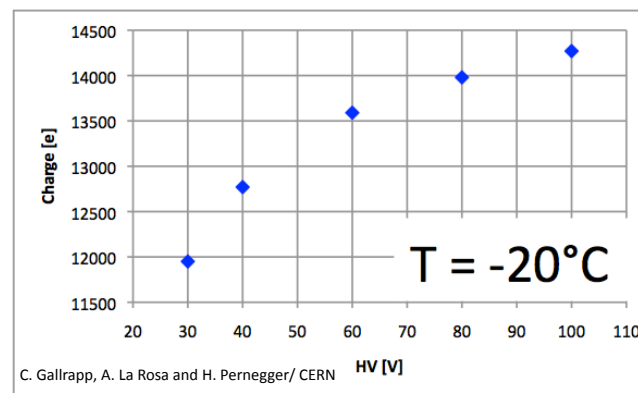
Detailed measurements with 3D/FBK are available at:

[CERN ATLAS Pixel R&D twiki page](#)

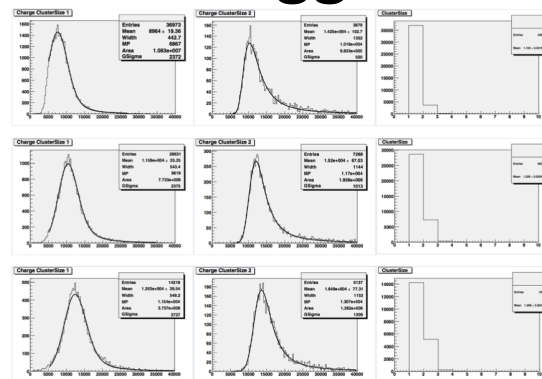
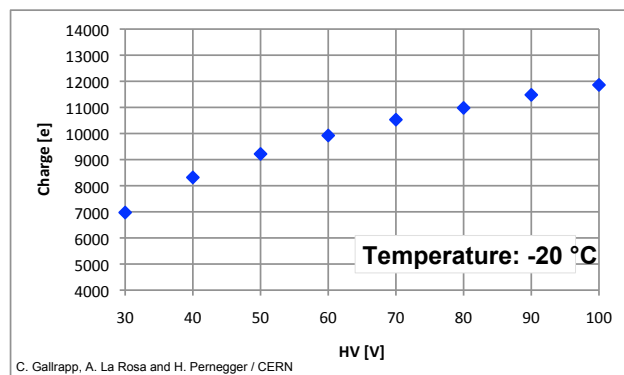
- γ -source (Am241 and Cd109) – self triggered



Am241
60keV



- β -source (Sr90) – external triggered



Bias voltage	30V	40V	60V	80V	100V
Lost charge	49%	40%	30%	21%	15%

25MeV proton irradiation
up to $5.4 \text{ e}^{14} \text{ p/cm}^2$
($1 \text{ e}^{15} \text{ n}_{\text{eq}}/\text{cm}^2$)